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Sheet 1 of 1

Complete if Known	
Application Number	10/677,643
Filing Date	10/01/2003
First Named Inventor	TOMISLAV SULIGOJ
Art Unit	
Examiner Name	
Attorney Docket Number	UC01-332-2US

NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No.[1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T[2]
		P. BILJANOVIC, T. SULIGOJ, "Horizontal Current Bipolar Transistor (HCBT): A New Concept of Silicon Bipolar Transistor Technology", IEEE Trans. on Electron Devices, 1 Nov. 2001, pp 2551-2554, vol. 48	
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Examiner Signature		Date Considered	

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